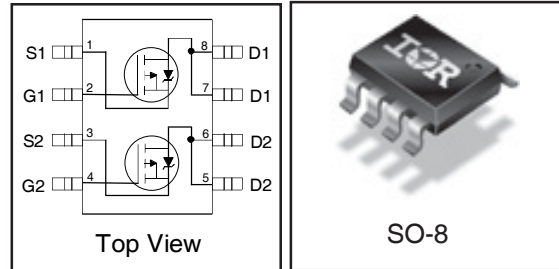


HEXFET® Power MOSFET

$V_{DS}$	<b>-55</b>	<b>V</b>
$R_{DS(on) \max}$ (@ $V_{GS} = -10V$ )	<b>0.105</b>	$\Omega$
$Q_g$ (typical)	<b>26</b>	<b>nC</b>
$I_D$ (@ $T_A = 25^\circ C$ )	<b>-3.4</b>	<b>A</b>



**Features**

Industry-standard pinout SO-8 Package
Compatible with Existing Surface Mount Techniques
RoHS Compliant, Halogen-Free
MSL1, Industrial qualification



**Benefits**

Multi-Vendor Compatibility
Easier Manufacturing
Environmentally Friendlier
Increased Reliability

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
IRF7342PbF-1	SO-8	Tape and Reel	4000	IRF7342TRPbF-1

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{DS}$	Drain- Source Voltage	-55	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	-3.4	A
$I_D @ T_C = 70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	-2.7	
$I_{DM}$	Pulsed Drain Current ①	-27	
$P_D @ T_C = 25^\circ C$	Power Dissipation	2.0	W
$P_D @ T_C = 70^\circ C$	Power Dissipation	1.3	
	Linear Derating Factor	0.016	W/°C
$V_{GS}$	Gate-to-Source Voltage	± 20	V
$V_{GSM}$	Gate-to-Source Voltage Single Pulse $t_p < 10\mu s$	30	V
$E_{AS}$	Single Pulse Avalanche Energy ②	114	
dv/dt	Peak Diode Recovery dv/dt ③	5.0	V/ns
$T_J, T_{STG}$	Junction and Storage Temperature Range	-55 to + 150	°C

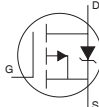
**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Maximum Junction-to-Ambient ④	—	62.5	°C/W

**Electrical Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)**

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-55	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.054	—	V/°C	Reference to $25^\circ\text{C}$ , $I_D = -1\text{mA}$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.095	0.105	$\Omega$	$V_{GS} = -10V, I_D = -3.4A$ ④
		—	0.150	0.170		$V_{GS} = -4.5V, I_D = -2.7A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	—	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
$g_{fs}$	Forward Transconductance	3.3	—	—	S	$V_{DS} = -10V, I_D = -3.1A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	-2.0	$\mu A$	$V_{DS} = -55V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -55V, V_{GS} = 0V, T_J = 55^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
$Q_g$	Total Gate Charge	—	26	38	nC	$I_D = -3.1A$
$Q_{gs}$	Gate-to-Source Charge	—	3.0	4.5		$V_{DS} = -44V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	8.4	13		$V_{GS} = -10V$ , See Fig. 10 ④
$t_{d(on)}$	Turn-On Delay Time	—	14	22	ns	$V_{DD} = -28V$
$t_r$	Rise Time	—	10	15		$I_D = -1.0A$
$t_{d(off)}$	Turn-Off Delay Time	—	43	64		$R_G = 6.0\Omega$
$t_f$	Fall Time	—	22	32		$R_D = 16\Omega$ , ④
$C_{iss}$	Input Capacitance	—	690	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	210	—		$V_{DS} = -25V$
$C_{rss}$	Reverse Transfer Capacitance	—	86	—		$f = 1.0\text{MHz}$ , See Fig. 9

**Source-Drain Ratings and Characteristics**

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	-27		
$V_{SD}$	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -2.0A, V_{GS} = 0V$ ③
$t_{rr}$	Reverse Recovery Time	—	54	80	ns	$T_J = 25^\circ\text{C}, I_F = -2.0A$
$Q_{rr}$	Reverse Recovery Charge	—	85	130	nC	$di/dt = -100A/\mu s$ ③

**Notes:**

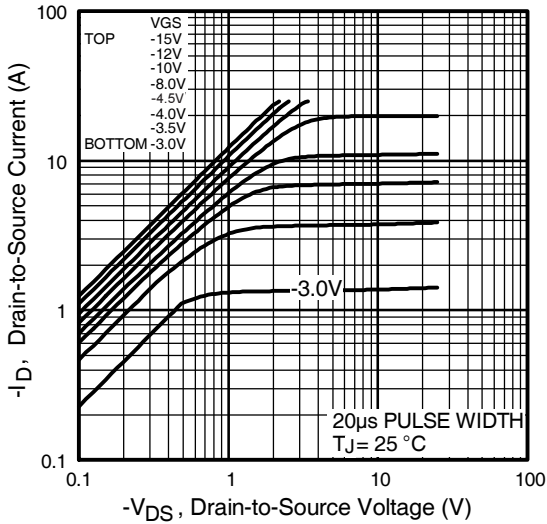
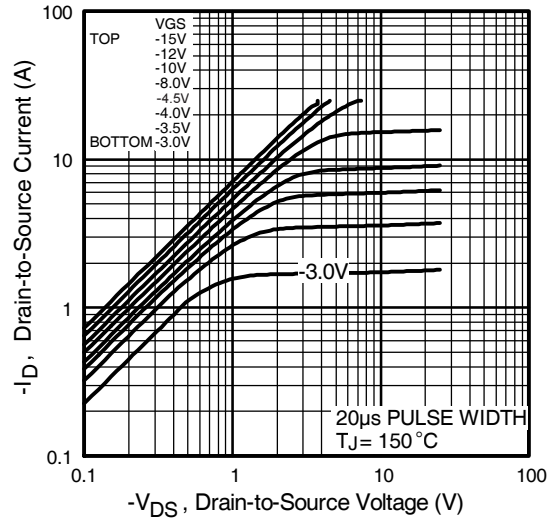
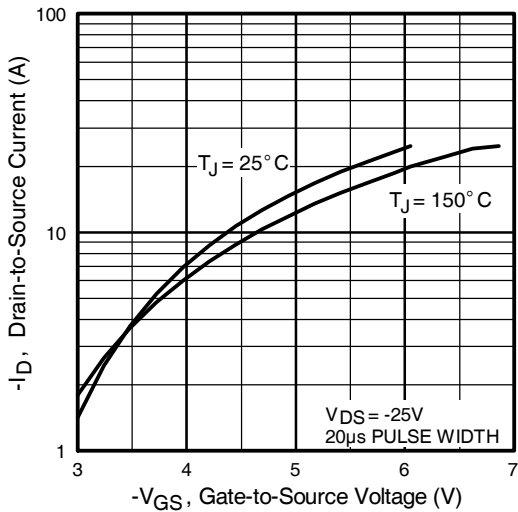
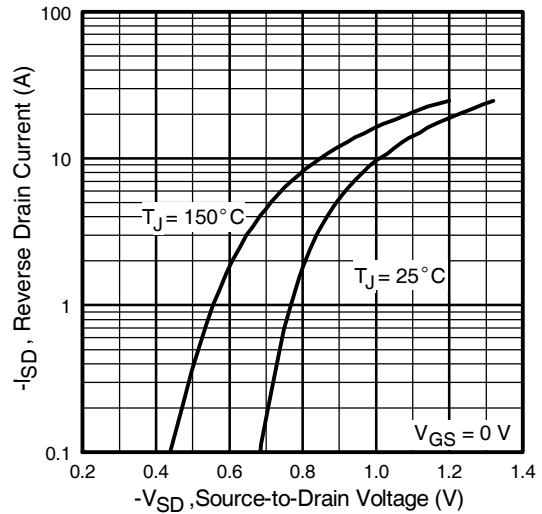
① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )

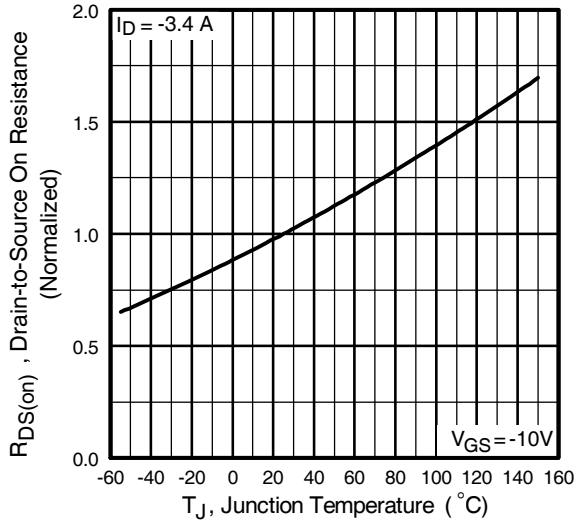
② Starting  $T_J = 25^\circ\text{C}$ ,  $L = 20\text{mH}$   
 $R_G = 25\Omega$ ,  $I_{AS} = -3.4A$ . (See Figure 8)

③  $I_{SD} \leq -3.4A$ ,  $di/dt \leq -150A/\mu s$ ,  $V_{DD} \leq V_{(BR)DSS}$ ,  
 $T_J \leq 150^\circ\text{C}$

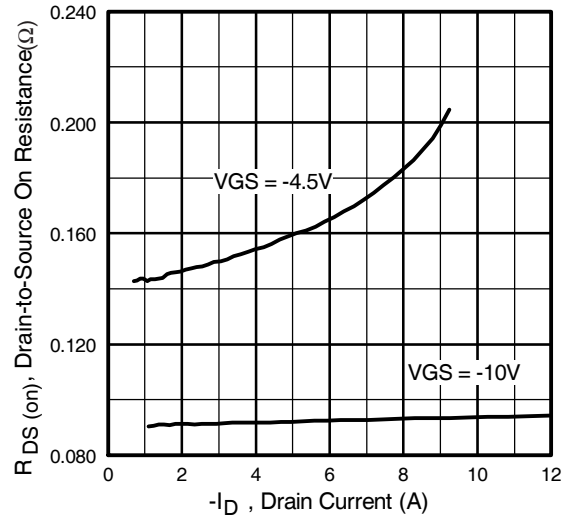
④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .

⑤ When mounted on 1 inch square copper board,  $t < 10$  sec

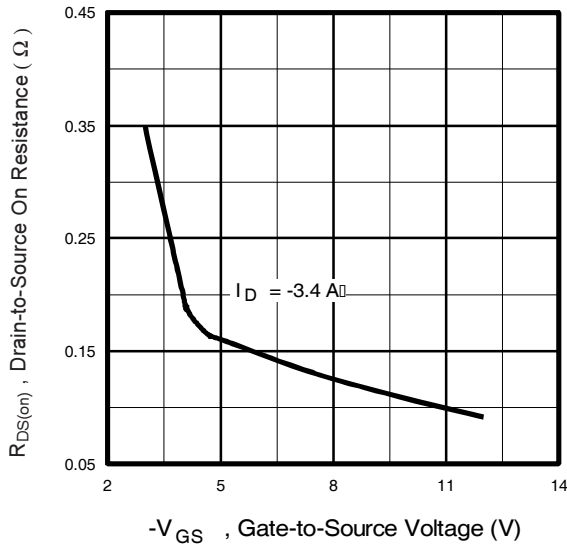

**Fig 1. Typical Output Characteristics**

**Fig 2. Typical Output Characteristics**

**Fig 3. Typical Transfer Characteristics**

**Fig 4. Typical Source-Drain Diode Forward Voltage**



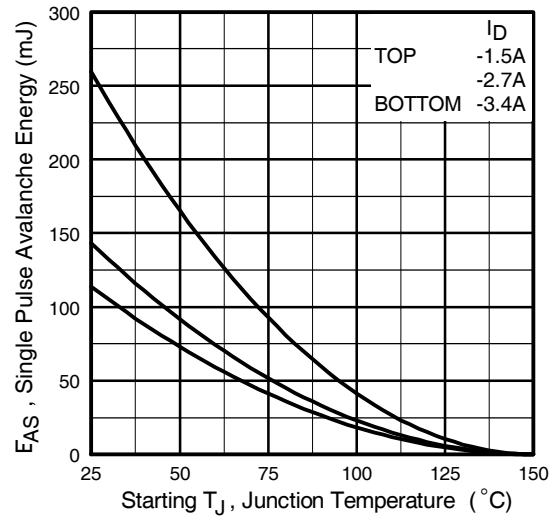
**Fig 5.** Normalized On-Resistance Vs. Temperature



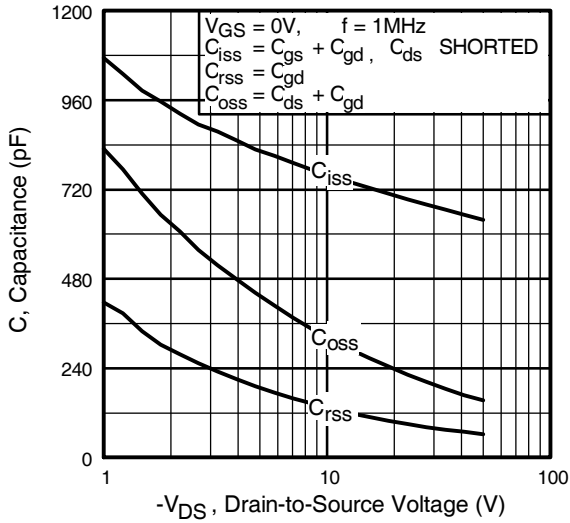
**Fig 6.** Typical On-Resistance Vs. Drain Current



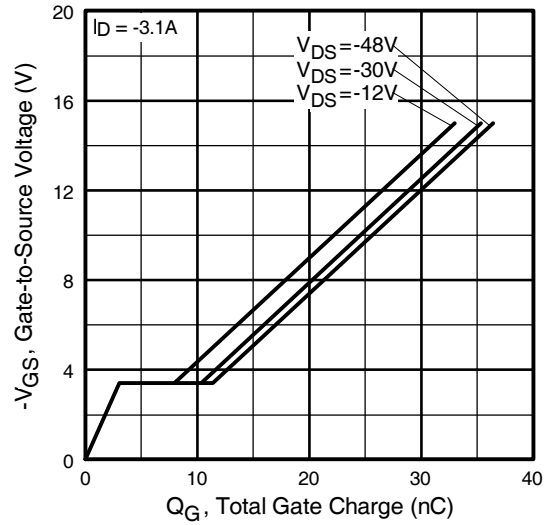
**Fig 7.** Typical On-Resistance Vs. Gate Voltage



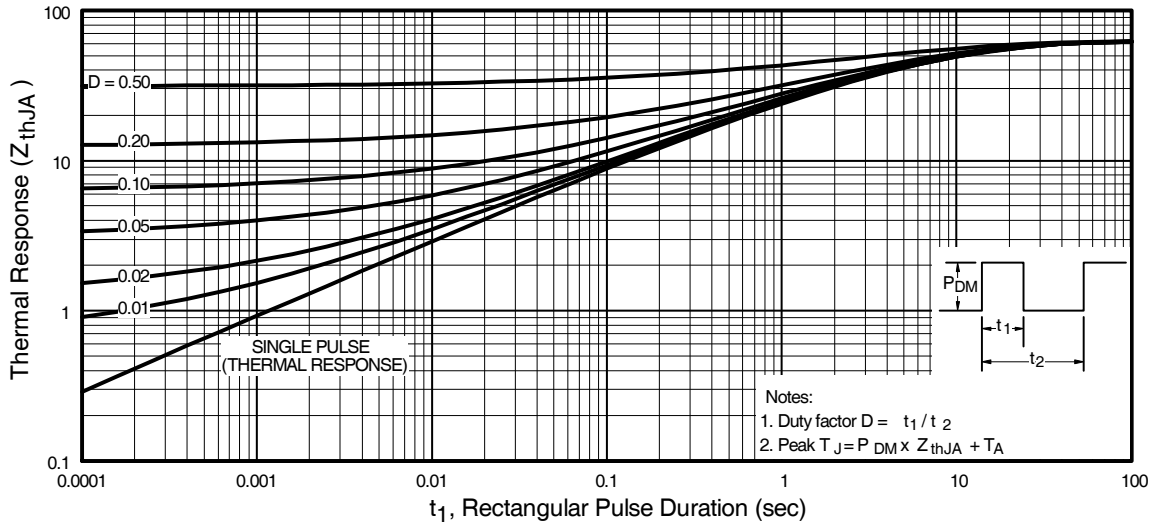
**Fig 8.** Maximum Avalanche Energy Vs. Drain Current



**Fig 9.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 10.** Typical Gate Charge Vs. Gate-to-Source Voltage

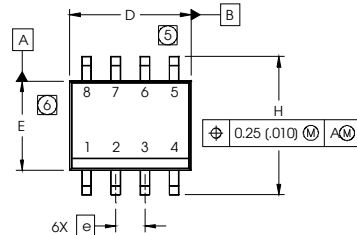


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

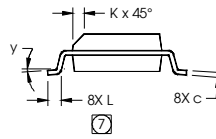
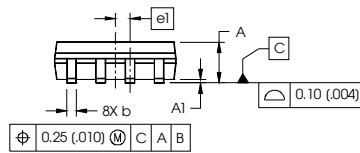


### SO-8 Package Outline

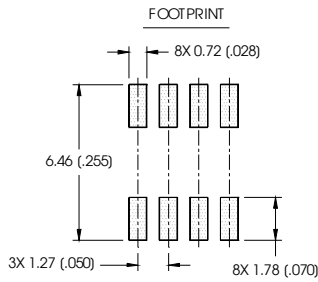
Dimensions are shown in millimeters (inches)



DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
AI	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
γ	0°	8°	0°	8°

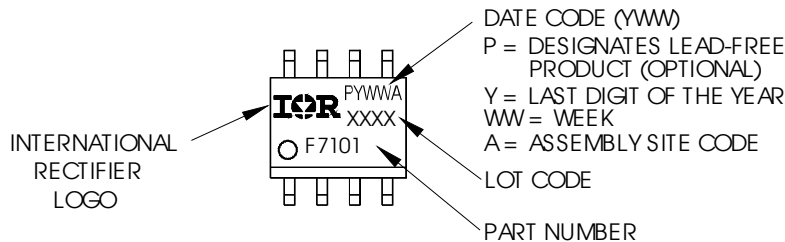


- NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
  2. CONTROLLING DIMENSION: MILLIMETER
  3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
  4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
  5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).
  6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).
  7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.

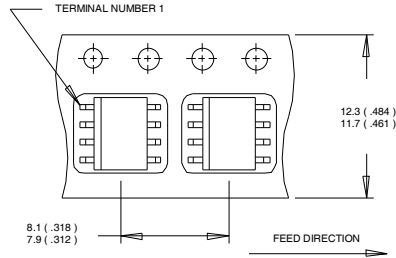


### SO-8 Part Marking Information (Lead-Free)

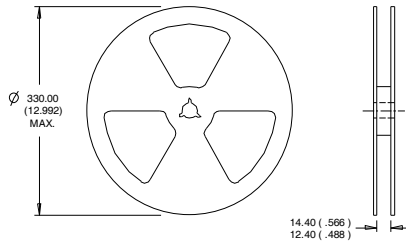
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

**SO-8 Tape and Reel** (Dimensions are shown in millimeters (inches))


- NOTES:  
 1. CONTROLLING DIMENSION - MILLIMETER.  
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).  
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



- NOTES:  
 1. CONTROLLING DIMENSION - MILLIMETER.  
 2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at: <http://www.irf.com/package/>

**Qualification information<sup>†</sup>**

Qualification level	Industriid (per JEDEC JESD47F <sup>††</sup> guidelines)	
Moisture Sensitivity Level	SO-8	M5L1 (per JEDEC J-STD-020D <sup>††</sup> )
RoHS compliant	Yes	

<sup>†</sup> Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

<sup>††</sup> Applicable version of JEDEC standard at the time of product release

**Revision History**

Date	Comments
10/16/2014	<ul style="list-style-type: none"> <li>Corrected part number from "IRF7342PbF-1" to "IRF7342TRPbF-1" -all pages</li> <li>Removed the "IRF7342PbF-1" bulk part number from ordering information on page1</li> </ul>